

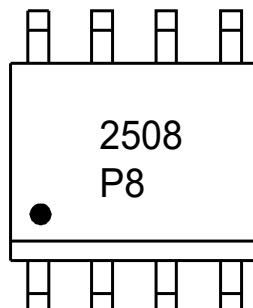
Description

The UL2508P8 is a low capacitance high power TVS, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The UL2508P8 complies with the IEC 61000-4-2 (ESD) standard with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into a 8-pin SOP-8 lead-free package. Each device will protect two line pairs high-speed lines. The combination of small size, low capacitance, and high surge capability makes them ideal for use in applications such as Gigabit Ethernet, telecommunication lines, and LVDS interfaces.

Features

- ◆ Low capacitance: 3pF typical
- ◆ Ultra low leakage: nA level
- ◆ Operating voltage: 2.5V
- ◆ Ultra low clamping voltage
- ◆ Protects up to eight lines
- ◆ Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
 - IEC 61000-4-5 (Lightning) 40A (8/20 μs)
- ◆ RoHS Compliant

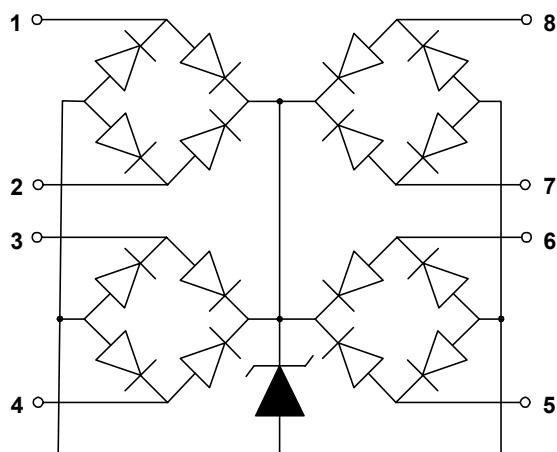
Marking Information



2508 P8= Device Marking Code

Dot denotes pin1

Dimensions and Pin Configuration



Applications

- ◆ LVDS Interfaces
- ◆ 10/100/1000 Ethernet
- ◆ Notebooks, Desktops, Servers
- ◆ Networking Equipment
- ◆ Switching Systems
- ◆ Audio/Video Inputs

Ordering Information

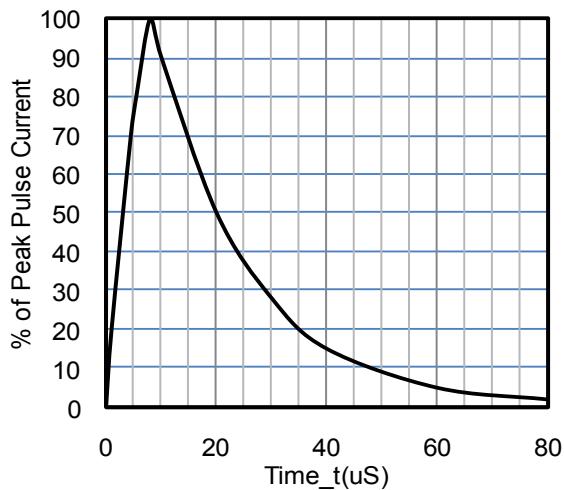
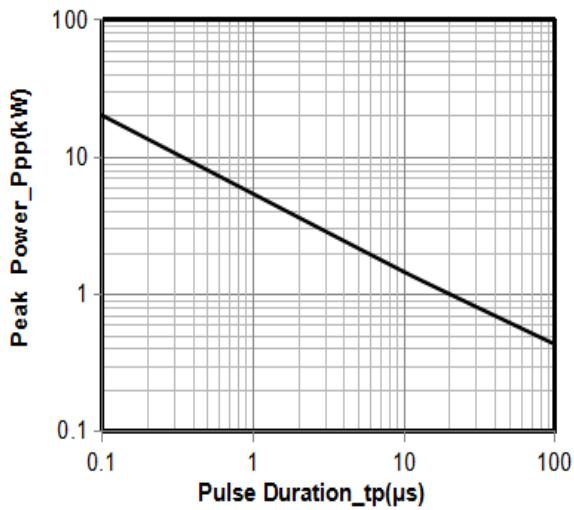
Part Number	Marking	Packaging	Reel Size
UL2508P8	2508 P8	2500/Tape & Reel	13 inch

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise specified)

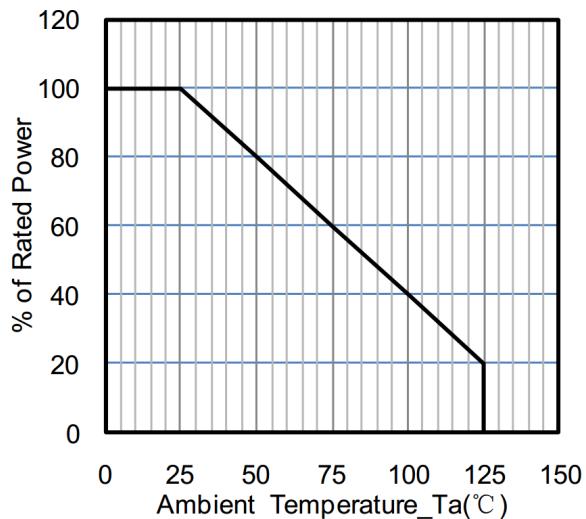
Parameter	Symbol	Value	Unit
Peak Pulse Power(8/20μs)	Ppk	1000	W
Peak Pulse Current(8/20μs)	Ipp	40	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	VESD	±30 ±30	kV
Operating Temperature Range	T _J	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +125	°C

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)

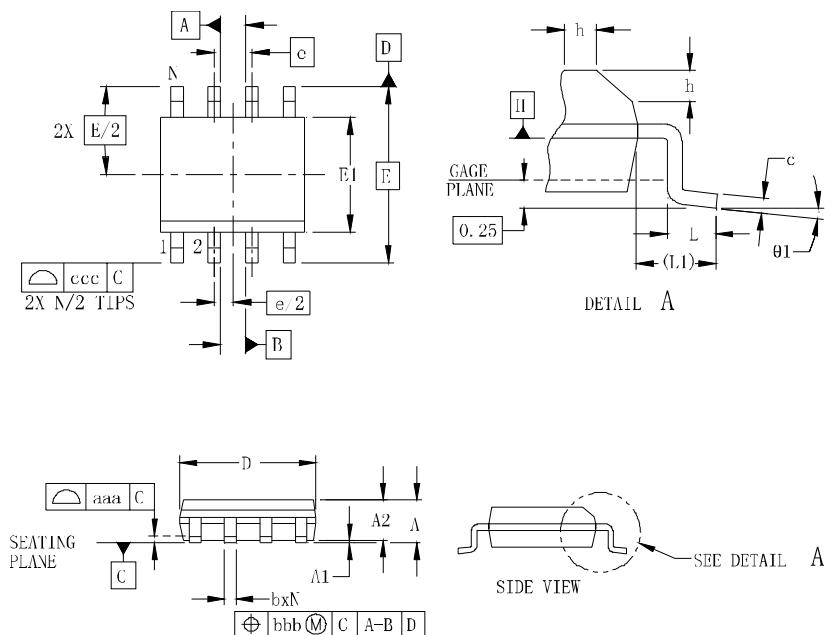
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			2.5	V	
Punch-Through Voltage	V _{PT}	3.0			V	I _T = 2μA
Snap-Back Voltage	V _{SB}	3.0			V	I _{SB} = 50mA
Reverse Leakage Current	I _R			0.1	μA	V _{RWM} = 2.5V
Clamping Voltage	V _C			7	V	I _{PP} = 1A (8 x 20μs pulse), I/O to I/O
Clamping Voltage	V _C			13	V	I _{PP} = 10A (8 x 20μs pulse), I/O to I/O
Clamping Voltage	V _C			24	V	I _{PP} = 25A (8 x 20μs pulse), I/O to I/O
Clamping Voltage	V _C			25	V	I _{PP} = 40A (8 x 20μs pulse), line to line (two I/O pins connected to- gether on each line)
Junction Capacitance	C _J			3.0	pF	VR = 0V, f = 1MHz, between I/O pins
Junction Capacitance	C _J			3.0	pF	VR = 0V, f = 1MHz, any line to line

Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)8 X 20 μs Pulse Waveform

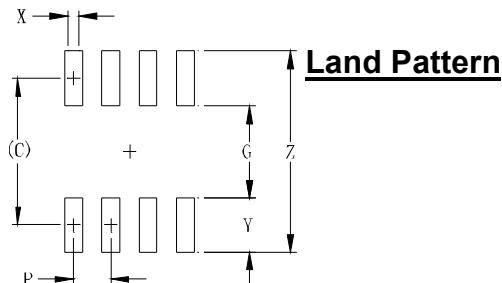
Peak Pulse Power vs. Pulse Time



Power Derating Curve

SO-8 Package Outline Drawing

SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.35		1.75	0.053		0.069
A1	0.10		0.25	0.004		0.010
A2	1.25		1.65	0.049		0.065
b	0.31		0.51	0.012		0.020
c	0.17		0.25	0.007		0.010
D	4.80	4.90	5.00	0.189	0.193	0.197
E1	3.80	3.90	4.00	0.150	0.154	0.157
E	6.00 BSC			0.236 BSC		
e	1.27 BSC			0.050 BSC		
h	0.25		0.50	0.010		0.020
L	0.40	0.72	1.04	0.016	0.028	0.041
L1	(1.04)			(0.041)		
N	8			8		
θ1	0°		8°	0°		8°
aaa	0.10			0.004		
bbb	0.25			0.010		
ccc	0.20			0.008		

Suggested

SYM	DIMENSIONS	
	MILLIMETERS	
	INCHES	INCHES
C	(5.20)	0.205
G	3.00	0.118
P	1.27	0.050
X	0.60	0.024
Y	2.20	0.087
Z	7.40	0.291